

ZXTP2029F 100V, SOT23, PNP medium power transistor

Summary

 $V_{(BR)CEV} > -130V$, $V_{(BR)CEO} > -100V$

 $I_{C(cont)} = -3A$

 $R_{CE(sat)} = 45 m\Omega$ typical

 $V_{CE(sat)} < -80 \text{mV} @ -1 \text{A}$

 $P_{D} = 1.2W$

Complementary part number ZXTN2020F



Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

Features

- Higher power dissipation SOT23 package
- · High peak current
- · Low saturation voltage
- · 130V forward blocking voltage

Applications

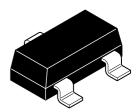
- · MOSFET and IGBT gate driving
- · Motor drive
- DC-DC converters
- · High side switches

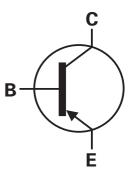
Ordering information

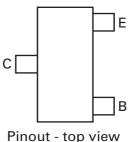
Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP2029FTA	7	8mm	3,000

Device marking

953







Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	-130	V
Collector-emitter voltage	V _{(BR)CEV}	-130	V
Collector-emitter voltage	V _{CEO}	-100	V
Emitter-base voltage	V _{EBO}	-7.0	V
Peak pulse current	I _{CM}	-5	А
Continuous collector current ^(a)	I _C	-3	А
Base current	I _B	-1	А
Power dissipation @ T _A =25°C ^(a) Linear derating factor	P _D	1.0 8.0	W mW/°C
Power dissipation @ T _A =25°C ^(b) Linear derating factor	P _D	1.2 9.6	W mW/°C
Power dissipation @ T _A =25°C ^(c) Linear derating factor	P _D	1.56 12.5	W mW/°C
Operating and storage temperature	T _j :T _{stg}	-55 to +150	°C

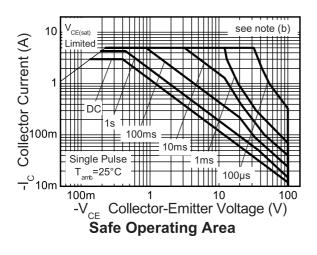
Thermal resistance

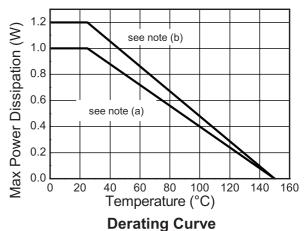
Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	$R\theta_{JA}$	125	°C/W
Junction to ambient ^(b)	$R\theta_{JA}$	104	°C/W
Junction to ambient ^(c)	$R\theta_{JA}$	80	°C/W

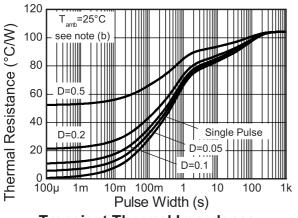
NOTES

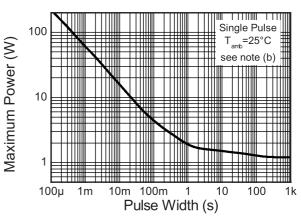
(a) Mounted on 18mm x 18mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions. (b) Mounted on 30mm x 30mm x 1.6mm FR4 PCB with a very high coverage of 2 oz weight copper in still air conditions. (c) As (b) above measured at t<5secs.

Characteristics



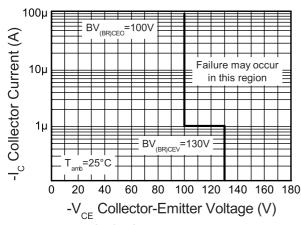






Transient Thermal Impedance

Pulse Power Dissipation



Safe Operating Area

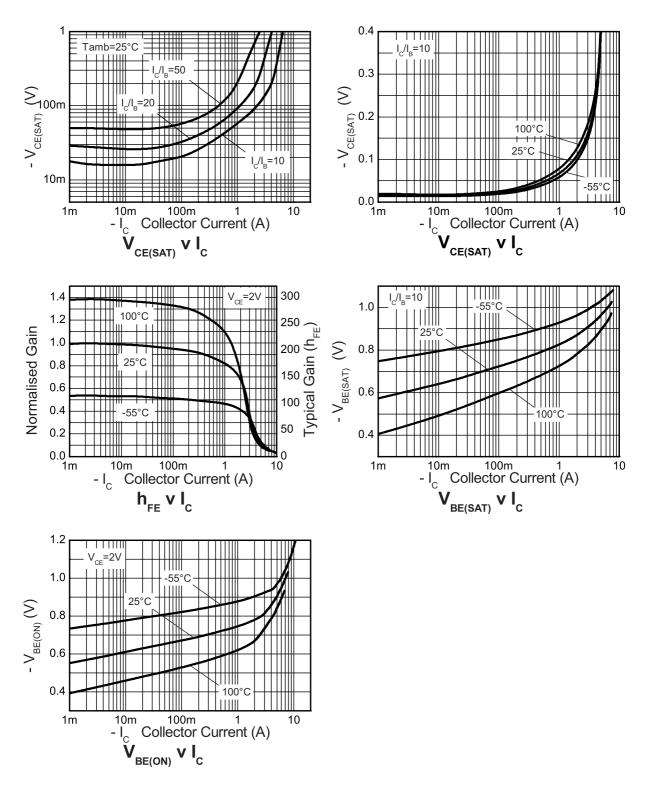
Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	V _{(BR)CBO}	-130	-160		V	I _C =-100μA
Collector-emitter breakdown voltage	V _{(BR)CEV}	-130	-160		V	$I_C = -1\mu A$, 1V> V_{BE} >-0.3V
Collector-emitter breakdown voltage	V _{(BR)CEO}	-100	-120		٧	I _C =-10mA ^(a)
Emitter-base breakdown voltage	V _{(BR)EBO}	-7.0	-8.3		٧	I _E =-100μA
Collector-emitter cut-off current	I _{CEV}			-20	nA	V _{CE} =-100V, V _{BE} = 1V
Collector-base cut-off current	I _{CBO}			-20	nA	V _{CB} =-100V
Emitter-base cut-off current	I _{EBO}			-10	nA	V _{EB} =-6V
Static forward current transfer ratio	H _{FE}	100 100 40	220 200 75	300		I _C =-10mA, V _{CE} =-2V ^(a) I _C =-1A, V _{CE} =-2V ^(a) Ic=-3A, V _{CE} =-2V
Collector-emitter saturation voltage	V _{CE(sat)}		-20 -60 -135 -180	-30 -80 -180 -250	mV mV mV	I _C =-100mA, I _B =-10mA ^(a) I _C =-1A, I _B =-100mA ^(a) I _C =-3A, I _B =-300mA ^(a) I _C =-4A, I _B =-400mA ^(a)
Base-emitter saturation voltage	V _{BE(sat)}		-0.90	-1.00	V	I _C =-3A, I _B =-300mA ^(a)
Base-emitter turn-on voltage	V _{BE(on)}		-0.81	-0.90	V	I _C =-3A, V _{CE} =-2V ^(a)
Transition frequency	f _T		150		MHz	Ic=-100mA, V _{CE} =-10V, f=50MHz
Output capacitance	C _{obo}		39		рF	V _{CB} =-10V, f=1MHz
Delay timetime	t _(d)		21		ns	V _{CC} =-10V, I _C =-1A,
Rise time	t _(r)		12		ns	I _{B1} =I _{B2} =-100mA
Storage time	t _(stg)		410		ns	
Fall time	t _(f)		35		ns	

NOTES

(a) Measured under pulsed conditions. Pulse width=300 $\mu S.$ Duty cycle $\leq\!2\%.$

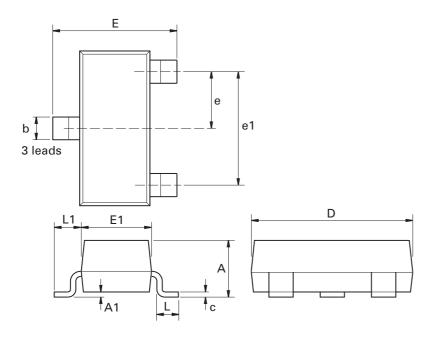
Typical characteristics



ZXTP2029F

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Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Мах.	Min.	Max.
Α	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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